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SERIAL NUMBER 10/612,642	FILING DATE 07/01/2003  RULE	CLASS 438	GROUP ART UNIT 2812	ATTORNEY DOCKET NO. 007612 USA/ETCH/SILICON
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## APPLICANTS

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## \*\* CONTINUING DATA \*\*\*\*\*

This appln claims benefit of 60/393,393 07/02/2002 *WLL*

## \*\* FOREIGN APPLICATIONS \*\*\*\*\*

*None WLL*

## IF REQUIRED, FOREIGN FILING LICENSE GRANTED

\*\* 09/26/2003

Foreign Priority claimed <input type="checkbox"/> yes <input checked="" type="checkbox"/> no	STATE OR COUNTRY CA	SHEETS DRAWING 11	TOTAL CLAIMS 30	INDEPENDENT CLAIMS 5
35 USC 119 (a-d) conditions met <input type="checkbox"/> yes <input checked="" type="checkbox"/> no <input type="checkbox"/> Met after Allowance <i>WLL</i>				
Verified and Acknowledged	Examiner's Signature	Initials		

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## TITLE

Method for fabricating an ultra shallow junction of a field effect transistor

☐ All Fees